

CMOS

Quad Clocked "D" Latch

High-Voltage Types (20-Volt Rating)

CD4042B types contain four latch circuits, each strobed by a common clock. Complementary buffered outputs are available from each circuit. The impedance of the n- and p-channel output devices is balanced and all outputs are electrically identical. Information present at the data input is transferred to outputs Q and \overline{Q} during the CLOCK level which is programmed by the POLARITY input. For POLARITY = 0 the transfer occurs during the 0 CLOCK level and for POLARITY = 1 the transfer occurs during the 1 CLOCK level. The outputs follow the data input providing the CLOCK and POLARITY levels defined above are present. When a CLOCK transition occurs (positive for POLARITY = 0 and negative for POLARITY = 1) the information present at the input during the CLOCK transition is retained at the outputs until an opposite **CLOCK** transition occurs.

The GD4042B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes); 16-lead dual*In-line plastic package (E suffix), and in chip form (H suffix).



CLOCK	POLARITY	٩			
0	0	D			
	0	LATCH			
1	1	D			
~	1	LATCH			
Fig. 1 — Logic block diagram and truth table,					

Features:

- Clock polarity control
 Q and Q outputs
- Common clock
- Low power TTL compatible
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 µA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin (over full package temperature range):

 - 1 V at V_{DD} = 5 V 2 V at V_{DD} = 10 V 2.5 V at V_{DD} = 15 V
- Meets all requirements of JEDEC Tentative Standard No. 138, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Buffer storage
- Holding register
- General digital logic







92CS-20756R TERMINAL ASSIGNMENT

CHARAC-	CONI		19	LIMI	TSAT	INDICA	TED TE	MPERA	TURES	(2 0)	UNITS
TERISTIC	Vo	Vini	Voo						+25		011113
	(V)	(V)	(V)	-55	40	+85	+125	Min.	Тур.	Max.	
Quiescent	_	0,5	5	1	1	30	30		0.02	1	
Device	_	0,10	10	2	2	60	60		0.02	2	
Current		0,15	15	4	4	120	120	-	0.02	4	~ ^
I _{DD} Max.	-	0,20	20	20	20	600	600	—	0.04	20	
Output Low					Ì						
(Sink)	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	_	
Current,	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	- ¹	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	mA
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	_	
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2		
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	0.9	-1.3	-2.6		
OH Min.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	6.8	· ·-	
Output Volt-							8 - P				
age:	-	0,5	5		0.0	05		-	0	0.05	
Low-Level,		0,10	10		0.0)5		-	0	0.05	÷
VOL Max.	-	0,15	15	1110	0.0)5		14	0	0.05	v
Output Volt-				1. 15 1. 1			· · · ·			1. 1	1 °
age :	_	0,5	5	10 J.M	4.9	95		4.95	5		
High-Level,	—	0,10	10		9.9	95		9.95	10		
V _{OH} Min.	-	0,15	15	le le	14.	95		14.95	15	-	
Input Low	0.5,4.5		5		1.	5		· -	_	1.5	
Voltage,	1,9	—	10	1. 	3	3		_		3	
VIL Max.	1.5,13.5	-	15		4	Ļ	24	-	—	4	v
Input High	0.5,4.5	_	5		3.	5		3.5	. –	_	
Voltage,	1,9	-	10	4	7			7	-	-	1
V _{1H} Min.	1.5,13.5	-	15		1	1		11	-	-	

STATIC ELECTRICAL CHARACTERISTICS

nput		0.40	10	10.4	10.1	4.4			+10-5	+0.1		
Current,	-	0,18	18	±0.1	±0.1	ΞI	TI	-	10 ¢	±0.1	μΑ	
IIN Max.												

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CD4042B Types

MAXIMUM	RATINGS,	Absolute-	Maximum	Values
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DC SUPPLY-VOLTAGE HANGE, (VDD)	
Voltages referenced to V _{SS} Terminal)	0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to VDD +0.5V
DC INPUT CURRENT, ANY ONE INPUT	±10mA
POWER DISSIPATION PER PACKAGE (PD):	
For $T_A = -55^{\circ}C$ to $+100^{\circ}C$	500mW
For T _A = +100°C to +125°C Derate Linearity at 1	2mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	
OPERATING-TEMPERATURE RANGE (TA)	55°C to +125°C
STORAGE TEMPERATURE RANGE (Tsta)	65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 + 1/32$ inch $(1.59 + 0.79 mm)$ from case for 10s max	+26500



DRAIN-TO-SOURCE VOLTAGE (VDS)-V 9205-2431883

Fig. 2 – Typical output low (sink) current characteristics.

operation is always within the following	ranges:				
CHARACTERISTIC	VDD	LIMITS		UNITS	
	(V)	Min.	Max.	1	
Supply-Voltage Range (For TA=Full Package Temperature Range)	-	3	18	v	
Clock Pulse Width, tw	5 10 15	200 100 60		ns	
Setup Time, t _S	5 10 15	50 30 25		ns	
Hold Time, t _H	5 10 15	120 60 50		ns	
Clock Rise or Fall Time: t _r , t _f	5,10 15	Not ris time se	e or fall ensitive.	μS	







Fig. 4 — Typical output high (source) current characteristics,



RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}C$, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that

-15 -10 ENT TEMPERATURE (TA)=25°C MGH (SOURCE OUTPUT





9265-2432182

Fig. 5 - Minimum output high (source) current characteristics.

9203-27635 Fig. 6 - Typical propagation delay time vs. load capacitance-data to Q.

9205-27636 Fig. 7 — Typical propagation delay time vs. load capacitance—data to $\overline{\Omega}$.

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DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}$ C; Input t_r , $t_f = 20$ ns, $C_L = 50$ pF, R_L = 200 K Ω

CHARACTERISTIC	VDD	LIM	UNITS		
	(0)	Тур.	Max.	1	
Propagation Delay Time: tpHL, tpLH	5 10 15	110 55 40	220 110 80	ns	
Data In to Q	5 10 15	150 75 50	300 150 100	ns	
Clock to Q	5 10 15	225 100 80	450 200 160	ns	
Clock to Q	5 10 15	250 115 90	500 230 180	ns	
Transition Time:tTHL, tTLH	5 10 15	100 50 40	200 100 80	ns	
Minimum Clock Pulse Width, t _W	5 10 15	100 50 30	200 100 60	ns	
Minimum Hold Time, t _H	5 10 15	60 30 25	120 60 50	ns	
Minimum Setup Time, t _S	5 10 15	0 0 0	50 30 25	ns	
Clock Input Rise or Fall Time: t _r , t _f	5,10 15	Not rise time se	e or fall nsitive.	μS	
Input Capacitance, C _{IN} Polarity Input	_	5	7.5	pF	
All Other Inputs	-	7.5	15	pF	



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Fig. 8 - Typical propagation dalay time vs. load capacitance-clock to Q



load capacitance-clock to \overline{Q} .





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AMBIENT TEMPERATURE (TA) - 25"C

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POLARITY IS NIGH.	92CS- 27401RI	9205-2744181
92CS-27630	VSS	
Fig. 12 – Dynamic test parameters.	Fig. 13 – Quiescent device current test circuit.	Fig. 14 - Input voltage test circuit.

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Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).



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